

NTE489

Silicon P-Channel JFET Transistor General Purpose AF Amplifier

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Gate-Drain Voltage (Note 1), V_{GD}	30V
Gate-Source Voltage (Note 1), V_{GS}	30V
Gate Current, I_G	-50mA
Total Device Dissipation ($T_A = +25^\circ\text{C}$), P_D	360mW
Derate Above 25°C	3.27mW/ $^\circ\text{C}$
Operating Junction Temperature Range, T_J	-55° to +135°C
Storage Temperature Range, T_{stg}	-55° to +150°C
Lead Temperature (During Soldering, 1/16" from case for 10sec), T_L	+300°C

Note 1. Geometry is symmetrical. Units may be operated with source and drain leads interchanged.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = 1\mu\text{A}, V_{DS} = 0$	30	-	-	V
Gate Reverse Current	I_{GSS}	$V_{GS} = 20\text{V}, V_{DS} = 0$, Note 2	-	-	200	pA
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$I_D = -1\text{nA}, V_{DS} = -15\text{V}$	0.5	-	2.0	V
Gate Current	I_G	$I_D = -2\text{mA}, V_{DG} = -15\text{V}$, Note 2	-	15	-	pA
Saturation Drain Current	I_{DSS}	$V_{DS} = -15\text{V}, V_{GS} = 0$	-2	-	-15	mA
Dynamic Characteristics						
Common-Source Forward Transconductance	g_{fs}	$V_{DS} = -15\text{V}, V_{GS} = 0, f = 1\text{kHz}$, Note 3	6000	-	15000	μmho
Common-Source Output Conductance	g_{os}	$V_{DS} = -15\text{V}, V_{GS} = 0, f = 1\text{kHz}$	-	-	200	μmho
Common-Source Input Capacitance	C_{iss}	$V_{DS} = -15\text{V}, V_{GS} = 0, f = 1\text{MHz}$	-	32	-	pF
Common-Source Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -15\text{V}, V_{GS} = 0, f = 1\text{MHz}$	-	4	-	pF
Equivalent Short-Circuit Input Noise Voltage	e_n	$V_{DS} = -10\text{V}, I_D = -2\text{mA}, f = 1\text{kHz}$	-	6	-	$\frac{\text{nV}}{\sqrt{\text{Hz}}}$

Note 2. Approximately doubles for every 10°C increase in T_A .

Note 3. Pulse test duration = 2ms.

